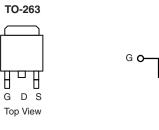


Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 60			
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.0067			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.0088			
I _D (A)	- 120			
Configuration	Single			



P-Channel MOSFET

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FEATURES

- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM110P06-07L-GE3		

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 60	v	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	$T_C = 25 \ ^{\circ}C^a$	- I _D -	- 120		
	T _C = 125 °C		- 102		
Continuous Source Current (Diode Conduction) ^a		I _S	- 120	A	
Pulsed Drain Current ^b		I _{DM}	- 480		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 80		
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	320	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	375	w	
	T _C = 125 °C	P _D	125		
Operating Junction and Storage Temperature Range	je	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/ W	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						L		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = - 250 μA		- 2.0	- 2.5		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = - 60 V	-	-	- 1		
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA	
		$V_{GS} = 0 V$	V_{DS} = - 60 V, T_{J} = 175 °C	-	-	- 250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 120	-	-	Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 30 A	-	0.0056	0.0067	Ω	
	Б	V _{GS} = - 10 V	I _D = - 30 A, T _J = 125 °C	-	-	0.0110		
	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 30 A, T _J = 175 °C	-	-	0.0120		
		V _{GS} = - 4.5 V	I _D = - 20 A	-	0.0076	0.0088		
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 30 A		-	90	-	S	
Dynamic ^b					-			
Input Capacitance	C _{iss}		0 V V _{DS} = - 25 V, f = 1 MHz	-	11 400	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	1200	-		
Reverse Transfer Capacitance	C _{rss}			-	900	-		
Total Gate Charge ^c	Qg		V _{DS} = - 30 V, I _D = - 110 A	-	230	-	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V		-	50	-		
Gate-Drain Charge ^c	Q _{gd}			-	60	-		
Gate Resistance	Rg	f = 1 MHz		1.1	2.27	3.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	20	-		
Rise Time ^c	t _r	V_{DD} = - 30 V, R _L = 0.27 Ω I _D \cong - 110 A, V _{GEN} = - 10 V, R _g = 1 Ω		-	23	-	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	97	-		
Fall Time ^c	t _f			-	32	-		
Source-Drain Diode Ratings and Char	acteristics ^b				•			
Pulsed Current ^a	I _{SM}			-	-	- 480	Α	
Forward Voltage	V _{SD}	I _F = - 100 A, V _{GS} = 0		-	- 1.1	- 1.4	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

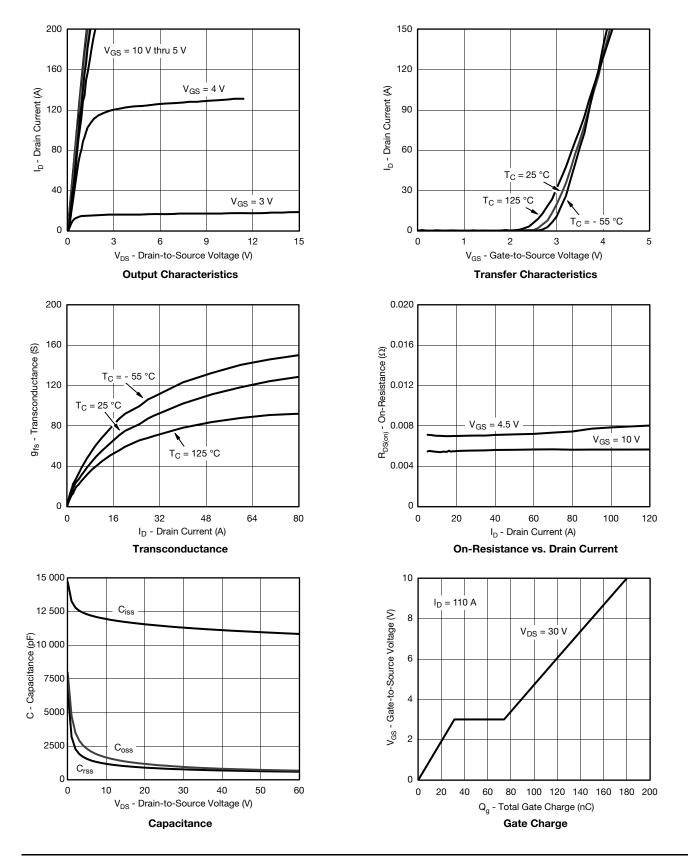
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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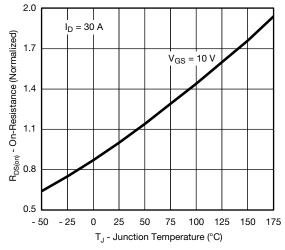
3 For technical questions, contact: automostechsupport@vishay.com Document Number: 65270

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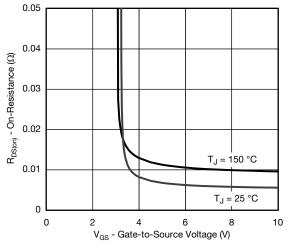
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



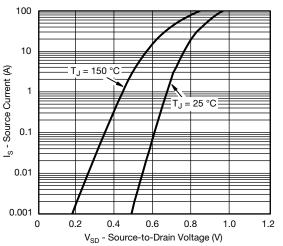
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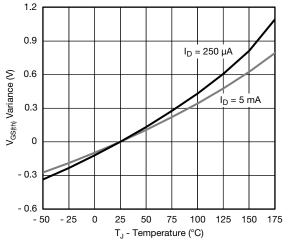
On-Resistance vs. Junction Temperature



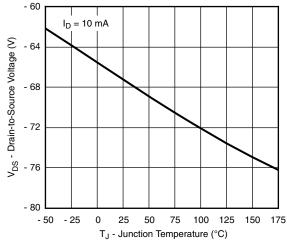
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

4

Document Number: 65270

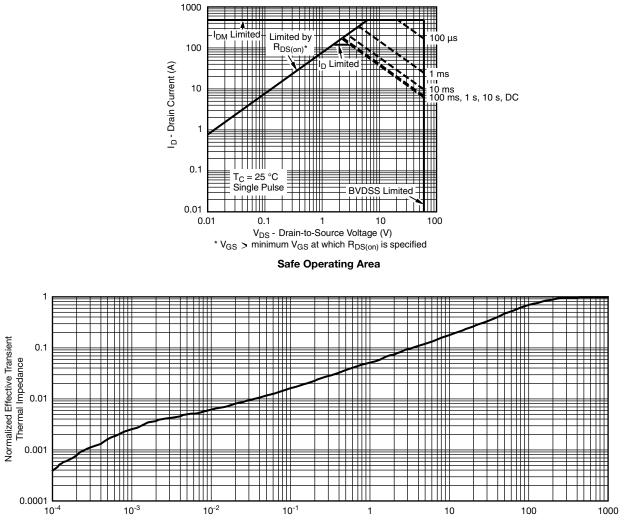
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



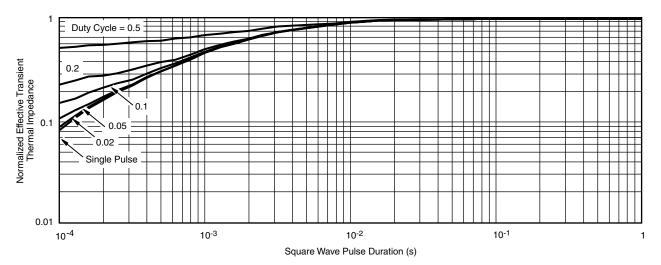
Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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